

isc N-Channel MOSFET Transistor

2SK382

DESCRIPTION

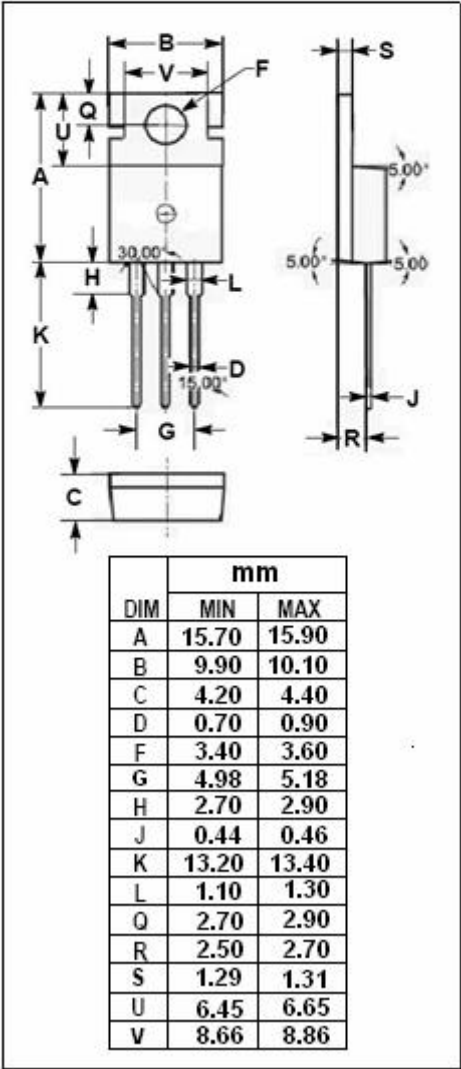
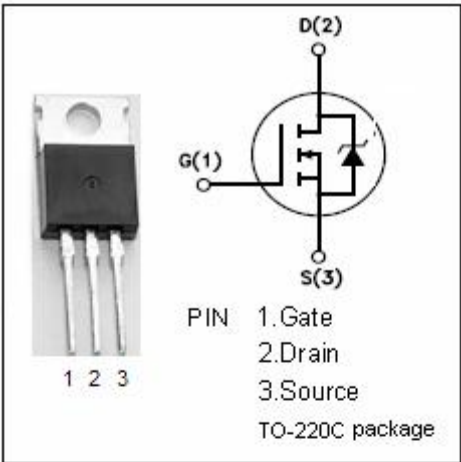
- Drain Current $-I_D=2A@ T_C=25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS}= 500V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

- High speed switching.
- High Cutoff frequency.
- No secondary breakdown.
- Suitable for switching regulator, DC-DC converter, RF amplifiers, and ultrasonic power oscillators.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	500	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=25^{\circ}C$	2	A
P_{tot}	Total Dissipation@ $TC=25^{\circ}C$	30	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc N-Channel Mosfet Transistor**2SK382****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	500			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = 10V _{GS} ; I _D = 1mA	2.0		5.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 15V; I _D = 1A		2.5	4.0	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±1	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =400V; V _{GS} = 0			1	mA
V _{SD}	Diode Forward Voltage	I _F = 1A; V _{GS} = 0		0.8		V
tr	Rise time	V _{GS} =15V; I _D =2A; R _L =15 Ω		18		ns
ton	Turn-on time			25		ns
tf	Fall time			25		ns
toff	Turn-off time			70		ns